TiberCAD User Manual

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TiberCAD User Manual

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Contents

Installation instructions

In the following, `VERSION` denotes the version number of the TiberCAD release you downloaded and `INSTALLPATH` denotes the directory where TiberCAD gets installed. Version 2.2.0 of GMSH (http://www.geuz.org/gmsh) will be installed together with TiberCAD. For the Linux version of GMSH you need OpenGL libraries installed on your system.

Prerequisites

Get the installer package for your OS/architecture from http://www.tibercad.org or by contacting support@tibercad.org. Table 1 lists the packages available for download. To run TiberCAD you will also need a license file that you will have to copy into the installation directory of TiberCAD.

In the Windows version, some graphical features such as graphical convergence monitors are only available if an X Window server is installed and running.

Windows installation procedure

To install TiberCAD in Windows, run the setup program `tibercad_setup.exe`. During the installation you can choose the installation directory. After finishing installation, copy your license file (tibercad.lic) into the `license` subdirectory of the TiberCAD installation directory (`INSTALLPATH/license`), without changing its filename.

installer package name	*Target architecture*
`tibercad_installer.exe`	Windows 32-bit
`tibercad_`*version*`_i386.deb`	Debian GNU/Linux 4.0 “etch”, Intel x86
`tibercad-`*version*`.tar.gz`	Generic Linux package

Table 1: Installer packages

Linux installation procedure

The installation procedure for the Linux version of TiberCAD depends on your distribution. Download the installer package that best fits your setup.

The standard method to launch TiberCAD is by means of a shell script that is installed alongside the TiberCAD executable. It takes care of setting all necessary environment variables. If for some reason you have to run the executable directly, remember to set `TIBERCADROOT` to the TiberCAD installation directory (`INSTALLPATH`) and `LD_LIBRARY_PATH` to `INSTALLPATH/lib`.

Debian

If you are running Debian GNU/Linux 4.0 "etch" on a i386 architecture, you can use the Debian package `tibercad_`*version*`_i386.deb`. Install it as root using dpkg or similar:

```
# dpkg --install tibercad_VERSION_i386.deb
```

The package will be installed in /usr/share/tibercad. Next, copy your license file (tibercad.lic) into /usr/share/tibercad/license/ without changing the filename.

NOTE: The debian version of TiberCAD depends on the following Debian packages:

- libboost-regex1.33.1
- libboost-filesystem1.33.1
- libblas.so.3 (provided e.g. by atlas3-base)
- liblapack.so.3 (provided e.g. by atlas3-base)

Other Linux distributions

If you have a distribution other than Debian 4.0 "etch" or you want to install TiberCAD into a different directory, then use the .tgz or .tbz installation packages. Unpack the archive, cd to the unpacked directory tibercad-`VERSION` and run the install script.

After installation, copy your license file (tibercad.lic) into the 'license' subdirectory of the TiberCAD installation directory (`INSTALLPATH`/license) without changing the filename.

Quick start guide

In the 'examples' subdirectory you can find several examples ready to run. They are the same as the tutorials on http://www.tibercad.org/documentation/tutorial/list.

Windows

Open Windows Explorer and go to the TiberCAD installation directory. If you have write permission in the installation directory, you can browse to an examples directory and start the simulation by double clicking the input file, e.g. bulk.tib in Example_0. If not, copy the whole directory to a location in your personal area and run the examples from there.

If you cannot run TiberCAD by double clicking an input file (*.tib), then the input files are probably not correctly associated with the TiberCAD executable. In this case, try to establish the association by right-clicking the input file, choosing `open with...` → `Choose Program...` → `Browse...`, browsing to the TiberCAD installation directory and choosing the TiberCAD executable, `tibercad.exe`. A directory containing the simulation results will be created with the name provided in the input file.

Linux

After the correct installation of TiberCAD you should be able to run TiberCAD from the command line using the command `tibercad`. If not, you probably have to add the `bin` subdirectory of the TiberCAD installation directory to your `PATH` environment variable or start the TiberCAD executable using the absolute path (`INSTALLPATH/bin/tibercad`). Copy the directory of the example you want to run, e.g. bulk_Si, to your home directory or any place you have write permissions for. Change to the newly created directory and run TiberCAD by (assuming Example_0)

```
$ tibercad bulk.tib
```

A directory containing the simulation results will be created with the name provided in the input file.

Bug reports / Feedback

Please send bug reports, feedback or suggestions to support@tibercad.org. When submitting bug reports, please always include the full version number of TiberCAD you are running. The full version number appears in the first line of output when running the program:

```
$ tibercad

TiberCAD version 1.0.0-961

Usage: tibercad <inputfile>
```

Chapter 1

Overview

1.1 Simulation models

TiberCAD is a multiphysics software tool; it includes several simulation models, each describing a physical problem to be solved, e.g. DriftDiffusion (to solve Poisson and DriftDiffusion equations), EFASchroedinger (to solve Schroedinger equation in envelope function approximation), Macrostrain (to calculate macroscopical strain with an elastic model) and others.

One **simulation** is a particular set of equations, boundary conditions, physical parameters, solver parameters, which describes a physical problem to be solved by TiberCAD. A valid TiberCAD **simulation** must belong to one of the predefined TiberCAD **simulation models** (see section 4.4).

To create a TiberCAD **simulation**, we first have to declare the TiberCAD **model** class to which our simulation belongs:

```
$Models
{
  model driftdiffusion
  {
    ...
```

Here, we declare that the simulation to be created will belong to the **model** class driftdiffusion (*model driftdiffusion*) In the next *Options* block, we define the **name** of the TiberCAD **simulation** (*simulationname* =) and the TiberCAD regions to which it will be applied (e.g., *physical_regions* = *all*, where 'all' means the whole device)

In general, several TiberCAD **simulations** belonging to the same **model** can be created; each of them must have a different name. As we will see in the following (see 4.5,4.6) , it is possible to specify physical and solver parameters for a single TiberCAD

simulation, by referring to its **name**. Anyway, it is also possible to specify parameters **common** to all the TiberCAD **simulations** belonging to the same **model**, by referring to the name of the TiberCAD model instead (in this case *'driftdiffusion'*).

1.2 Simulation environments

TiberCAD allows to compute different physical models in different parts of a device or nanostructure by coupling in a general way different *simulation environments*. A *simulation environment* is composed by all the physical regions to which a particular model is assigned. A *simulation environment* is therefore defined by the mesh elements belonging to its physical regions and by the **simulation model** which has been associated to these regions. This association is made possible by the definition of TiberCAD **Regions** and **Clusters**. Different *simulation environments* can have physical regions in common. In this way, each simulation is run on a subset of the device and can be possibly coupled (even self-consistently) with a simulation run on a different subset of the device corresponding to a *simulation environment* with a non-void intersection with the first one. The coupling of the two simulations is performed by means of appropriate Boundary Conditions (e.g. Current Density, Voltage, ...) In principle, the two *simulation environments* can refer to two simulations at different scale , e.g. atomistic tight-binding and macroscopic drift-diffusion. This allows an effective **multi-scale** simulation of the device to be studied.

1.3 Physical and boundary regions in TiberCAD

When TiberCAD is run, it reads the mesh file which contains the finite element grid which meshes the geometrical description of the device or nanostructure, and which will be the basis of PDE discretization.

To execute the proper simulations, TiberCAD needs some information about the physical and boundary regions associated with the mesh: a physical region associates all the elements corresponding to an homogeneous part of the device (usually related to the same material or doping). In TiberCAD, these regions are referred to as **mesh_regions** . Boundary regions are needed to specify boundary conditions (b.c.) for the solution of the PDEs of our simulation. By default, to all the external boundary of the device a Neumann b.c. is imposed, meaning null derivative of electric field and zero flux of current normal to the boundary. These are the usual b.c. applied in the simulation of electronic devices; in particular, these conditions are implicitly satisfied by using the finite element formulation.. Usually, one needs to impose also specifical b.c. to the device, relative, most often, to contacts of some kind (ohmic, schottky), but also heat and temperature b.c. or reference substrates for strain calculations. These regions, (constituted by surfaces ,

lines or points, respectively for 3D , 2D and 1D simulations) are referred to in TiberCAD with the keyword **BC_reg_numb**.

It is important to know that the information about the physical and boundary regions must be present in the mesh file before it is read by TiberCAD, and thus have to be produced by making use of the modeling/mesher software. As for now, TiberCAD supports the mesh output of the following software tools: **GMSH v.2** and **ISE-TCAD v.9.5**.

By means of the utility DEVISE of ISE-TCAD v.9.5, it is possible to design and mesh a device; after the meshing has been successfully performed, an output file is produced, with the extension *.grd*. This file contains the description of the mesh and also the list of the user defined material regions and contact regions. By reading this *.grd* file in TiberCAD, one can refer to the ISE TCAD material regions, simply with the user-defined name, which is present in the *.grd* file. This name should be unique in the whole device. In the same way, ISE TCAD Boundary regions (*Contacts*) can be referred to in TiberCAD by means of their user-defined name, present in the *.grd* output file, too.

If GMSH program is used to model and mesh the device, a bit more care has to be taken. Please see the GMSH user manual (http://geuz.org/gmsh) for further details. In the context of GMSH, it is possible to define several 1, 2 and 3D *Physical Entities*. These *Physical Entities* allow to associate one or more geometrical entities to a single numerical ID, so that several **mesh_regions** and **BC_reg_numb** can be defined and referred to by TiberCAD. Here is a simple example of a script to generate a 1D geometrical model (**.geo*) file in GMSH: (see also chapter 2)

```
Point(1) = {-25,0,0,0.5};
Point(2) = {0,0,0,0.002};
Point(3) = {25,0,0,0.5};
Line(1) = {1,2};
Line(2) = {2,3};


Physical Line(1) = {2};
Physical Line(2) = {1};
Physical Point(1) = {3};
Physical Point(2) = {1};
```

Here, first the geometrical entities **Point**s and **Line**s are defined.

In the definition of the geometrical **Points**, the three first expressions inside the braces on the right hand side give the three X, Y and Z coordinates of the point ; the last expression (0.5 or 0.002 in this example) sets the **characteristic mesh length** at that point, that is the **size** of a mesh element, defined as the length of the segment

for a line segment, the radius of the circumscribed circle for a triangle and the radius of the circumscribed sphere for a tetrahedron. Thus, the smaller is the value of the **characteristic mesh length**, the greater is the mesh density close to that point. The size of the mesh elements will then be computed in GMSH by linearly interpolating these characteristic lengths in the whole mesh.

In the definition of a geometrical **Line**, the two expressions inside the braces on the right hand side give the identification numbers of the start and end **Points** of the line;

Then, two physical regions are defined, each associated to one of the two geometrical entities: **Physical Line(1)** and **Physical Line(2)**. The expression(s) inside the braces on the right hand side give, in general, the identification numbers of all the geometrical lines that need to be grouped inside the **Physical Line**.

In this way, these physical regions are made available for TiberCAD, and will be used to associate them to a TiberCAD region through the keyword **mesh_regions** , as follows:

```
Region reg_1
   {
     mesh_regions  = 1

.............

Region  reg_2
   {
     mesh_regions  = 2

...........
```

Then, in the GMSH script, two **Physical Point** are defined, **1** and **2**, and associated to the first and to the last point of our 1D device. These points are needed to impose some boundary conditions and in this way they are made available for TiberCAD, and will be used to associate each of them to a boundary condition region, through the keyword **BC_reg_numb**

```
BC_Regions
    {
      BC_Region cathode
      {
        BC_reg_numb = 1

......................
```

```
BC_Region anode
        {
          BC_reg_numb = 2

.....................
```

In 2D case, a set of **Physical Surface** will be defined to be used as **mesh_regions**, while **Physical Line** is used for boundary conditions.

Finally, in 3D case, **Physical Volume** is used to define **mesh_regions**, while **Physical Surface** is used to define boundary conditions.

Chapter 2

Getting started 1D

In this section we will see, step by step, how to use TiberCAD to simulate numerically a semiconductor device. As a very simple example we will refer to the **Tutorial 0** (Si bulk) that you can find in the *Tutorials* directory.

Step 1: Modeling the device

As a first step, we have to model the device. To do so, you can use DEVISE module of ISE-TCAD 9.5 software package or GMSH program. Here we'll see in details the procedure for GMSH. There are two possible ways to use GMSH:

1. Interactive, using the graphical interface
2. Using a script file.

In the following we'll see how to write a basic GMSH script (bulk.geo); for any details please refer to GMSH manual GMSH (http://geuz.org/gmsh/).

In a GMSH script, several variables can be defined and given a value in this way:

```
L = 1;
d = 0.01;
```

these are valid GMSH variables: L is just the length of the Si sample; d is the value of a **characteristic mesh length** (see below).

- Definition of geometrical entities **Points**:

```
Point(1) = {0, 0, 0, d};
Point(2) = {L, 0, 0, d};
```

In the definition of a geometrical point, the three first expressions inside the braces on the right hand side give the three X, Y and Z coordinates of the point ; the last expression *(d)* sets the **characteristic mesh length** at that point, that is the **size** of a mesh element, defined as the length of the segment for a line segment, the radius of the circumscribed circle for a triangle and the radius of the circumscribed sphere for a tetrahedron.

Thus, the smaller is the value of *d,* the greater is the mesh density close to that point. The size of the mesh elements will then be computed in GMSH by linearly interpolating these characteristic lengths in the whole mesh.

- Definition of geometrical entity **Line**:

```
Line(1) = {1, 2};
```

The two expressions inside the braces on the right hand side give the identification numbers of the start and end points of the line.

- Definition of the physical entity **Physical Line 1**:

```
Physical Line(1) = {1};
```

The expression(s) inside the braces on the right hand side give the identification numbers of all the geometrical lines that need to be grouped inside the **physical line**. In this way, in general, **physical regions** are created which associate together geometrical regions, and then the related mesh elements, which share some common physical properties. It's only these physical regions which can be referred to outside GMSH. In TiberCAD, this is done by associating one or more physical regions to a **TiberCAD region** through the keyword **mesh_regions** (see in the following).

- Definition of two physical entities **Physical Point**:

```
Physical Point(1) = {1};
Physical Point(2) = {2};
```

N.B.: In general, in a *nD* simulation, *(n-1)D* physical regions (points in 1D, lines in 2D, surfaces in 3D) are used by TiberCAD to impose the required boundary conditions. Each *(n-1)D* physical region defined in this way in GMSH will be associated in TiberCAD to a boundary condition region, through the keyword **BC_reg_numb**. Thus, in this case, Physical points **1** and **2** will be associated respectively to two BC regions (see in the following).

Step 2: Meshing the device

The *.geo* script file with the geometrical description can be run in GMSH, to display the modelled device and to mesh it through the GMSH graphical interface. Alternatively, a *non-interactive* mode is also available in GMSH, without graphical user interface. For example, to mesh this 1D tutorial in non-interactive mode, just type:

gmsh bulk.geo -1 -o bulk.msh

where *bulk.geo* is the geometrical description of the device with GMSH syntax; *-1* means 1D mesh generation;

some command line options are:

-1, -2, -3 to perform 1D, 2D or 3D mesh generation,

-o mesh_file.*msh* to specify the name of the mesh file to be generated

In this way, a *.msh* has been generated and is ready to be read in TiberCAD.

Step 3: TiberCAD Input file

Now we have to write down the TiberCAD **input file** (see *bulk.tib* in the Tutorials).

1 - Definition of Device Regions

First, we have to list all the TiberCAD Regions present in our Device: a TiberCAD **Region** is usually a section of the device featuring the same material and possibly the same doping.

```
$Device
{
Region bulk
{
mesh_regions = 1
material = Si
doping = 1e16 doping_type = donor
}

}
```

The TiberCAD **Region** bulk is made of Silicon and n-doped with a concentration $10^{16} cm^{-3}$.

Through the keyword **mesh_regions** , one or more of the *physical regions* (*Physical Lines* in 1D, *Physical Surfaces* in 2D, *Physical Volumes* in 3D) previously defined in the GMSH mesh can be associated to the present TiberCAD **Region**.

With *mesh_regions = 1*, we associate the Physical Line 1, defined in the Step 1, to the TiberCAD **Region** *bulk*.

2 - Definition of Simulation

Now we define the **Simulation** *driftdiffusion_1*: it belongs to the class **driftdiffusion**

```
Models
{
model driftdiffusion
{
options
{
simulation_name = driftdiffusion_1
physical_regions = all
}
```

The TiberCAD **simulation** *driftdiffusion_1* , belonging to the **model driftdiffusion**, will be applied to the whole device structure (*physical_regions = all*).

3 - Definition of Boundary Conditions

The anode and cathode contacts of our 1D Si sample are defined as **Boundary conditions regions** (*BC_Region anode , BC_Region cathode*) in the following way:

```
BC_Region anode
{
BC_reg_numb = 1
type = ohmic
voltage = @Vb
}

BC_Region cathode
{
BC_reg_numb = 2
type = ohmic
voltage = 0.0
}
```

Both contacts are defined as *ohmic*, cathod is assigned a fixed *voltage = 0.0*, while anode voltage is given by the value of the variable *Vb (voltage = @Vb)*.

Through the keyword **BC_reg_numb** , one or more of the **(n-1)D** physical regions (Physical Points in 1D, Physical Lines in 2D, Physical Surfaces in 3D) previously defined in the GMSH mesh can be associated to the present TiberCAD **BC Region**. With *BC_reg_numb = 1*, we associate the Physical Point 1, defined in the **Step 1**, to the TiberCAD **BC Region** *anode*; with *BC_reg_numb = 2*, we associate the Physical Point 2, defined in the **Step 1**, to the TiberCAD **BC Region** *cathode*.

4 - Definition of Simulation parameters

The variable *Vb* is specified in the *sweep* block, in the **Solver** section

```
 sweep
{
simulation = driftdiffusion_1
variable = Vb
start = 0.0
stop = 1
steps = 10
}
```

In this way, the simulation *driftdiffusion_1* is performed for 10 (*steps = 10*) values of the anode voltage (*variable = Vb*), between 0 and 1.

5 - Definition of Execution parameters

In the **Simulation** section , we decide *which* simulations to perform and in which *order*; we set *solve = sweep*, to execute the *sweep* which run *driftdiffusion_1* **simulation** for the specified loop.

```
  $Simulation
{
#searchpath = .
meshfile = bulk.msh
dimension = 1
temperature = 300
solve = sweep
resultpath = output
output_format = grace
plot = (Ec, Ev, ContactCurrents)
}
```

Output files with conduction and valence band profiles (*plot = Ec,Ev..*) and all the calculated values of the current at the contacts (*ContactCurrents*) (the IV characteristic) are generated.

Step 4: Run TiberCAD

Now we can run TiberCAD:

```
tibercad bulk.tib
```

The generated **Output** files are:
driftdiffusion_materials.dat: *material* (mesh) regions, in this case just region 1
driftdiffusion_nodal.dat: *nodal* quantities (here conduction and valence band)
sweep_driftdiffusion_Vb.dat : *integrated current* at the two contacts for each sweep step.

Chapter 3

Getting started 2D

In this second example we will refer to the **Tutorial 4** (Si n-Mosfet) that you can find in the *Tutorials* directory.

Step 1: Modeling the device

Again, as a first step, we have to model the device.

We'll see in some details how to design and mesh a mosfet device with GMSH.

- In the GMSH script *mosfet.geo* , several variables are defined and given a value in this way:

```
lsub=0.03;
lacc=0.002;
lct=0.0005;
lg=0.0015;
lh=0.01;
lc=0.0005;
```

these variables are used in the script to assign proper values to the **mesh characteristic lengh** of the defined Points

```
Lg_2 = 0.0375;
d = 0.01;
Ls = 0.1;
h = 0.25;
b = 0.0025;
o = 0.005;
```

```
xd = Lg_2 + d;
xd2 = Lg_2 + d / 2;
xmax = xd + Ls - d;
```

These other convenient variables are used to parametrize the most relevant geometrical features, such as channel length, oxide thickness, and so on.

```
Point(1) = {0, -h, 0, lsub};
Point(2) = {0, 0, 0, lc};
Point(3) = {xmax,-h,0.0,lsub};
Point(4) = {-xmax,-h,0.0,lsub};
Point(5) = {xmax,0,0.0,lh};
Point(6) = {-xmax,0,0.0,lh};
.........................
Line(1) = {4,1};
Line(2) = {3,13};
Line(6) = {4,14};
Line(7) = {10,9};
Line(8) = {12,2};
Line(9) = {8,7};
Line(10) = {11,8};
Line(11) = {9,12};
Line(13) = {7,6};
.........................
```

- Geometrical **Points** and **Lines** are defined to design the device structure; the fourth parameter in **Point** assignement is the characteristic length associated to that point: this is an essential feature to control the mesh density and refine it where necessary (usually n the channel region).

```
Line Loop(40) = {28,2,-34,33,8,29,-31,-30,-6,1};
Plane Surface(41) = {40};
.........................
```

- Definition of a surface: first a **line loop** is composed, listing all the lines constituting the boundary of the surface; then this line loop is assigned to a **Plane Surface** object (this procedure can be alternatively performed throgh the graphical interface).

```
Physical Surface(1) = {41}; // n-Si
Physical Surface(2) = {44,47}; // n+-Si
Physical Surface(3) = {46}; // SiO2
```

- Definition of the **Physical surfaces** : each of them is composed by one or more geometrical **Plane Surface**. For example, **Physical surface** 2 comprises the two separated contact regions, while **Physical surface** 3 corresponds to the oxide region.

  The **Physical surfaces** are the 2D Physical regions of the mesh and will be assigned to the related TiberCAD regions through the keyword *mesh_regions* (see Step)

```
Physical Line(1) = {13}; // source
Physical Line(2) = {39,38}; // gate
Physical Line(3) = {19}; // drain
```

- Definition of the **Phisical Lines**: In this 2D simulation, 1D physical regions are used to carry information about boundary condition regions. In other word, each **Phisical Line** corresponds to a boundary condition (a contact in the case of a driftdiffusion calculation): thus Physical Line 1 refers to source contact, P.L. 2 to gate contact, P.L. 3 to drain contact. The numerical identifications of these **Phisical Lines** will be asigned to TiberCAD **BC regions** by means of the *BC_reg_numb* instruction.

In fig. 3.1 the obtained geometrical model is shown.

Step 2: Meshing the device

The *.geo* script file with the geometrical description can be run in GMSH, to display the modelled device and to mesh it through the GMSH graphical interface (see fig. 3.2). Alternatively, a *non-interactive* mode is also available in GMSH, without graphical user interface. For example, to mesh this 2D tutorial in non-interactive mode, just type:

gmsh mosfet.geo -2 -o mosfet.msh

Step 3: TiberCAD Input file

Now we have to write down the TiberCAD **input file** (see *mosfet.tib* in the Tutorials).

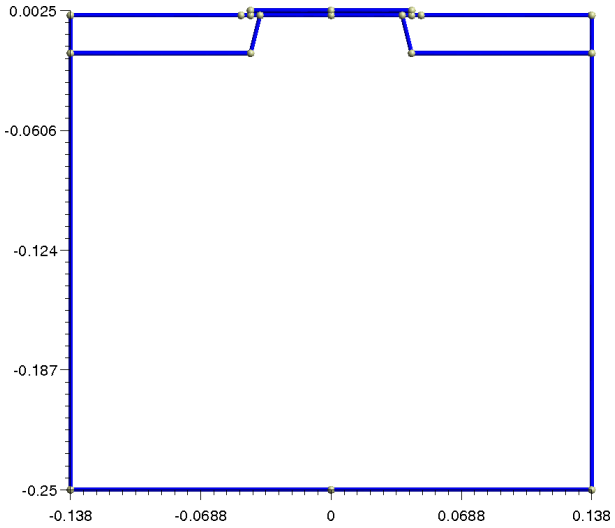

Figure 3.1: Geometrical structure as defined by GMSH modeller

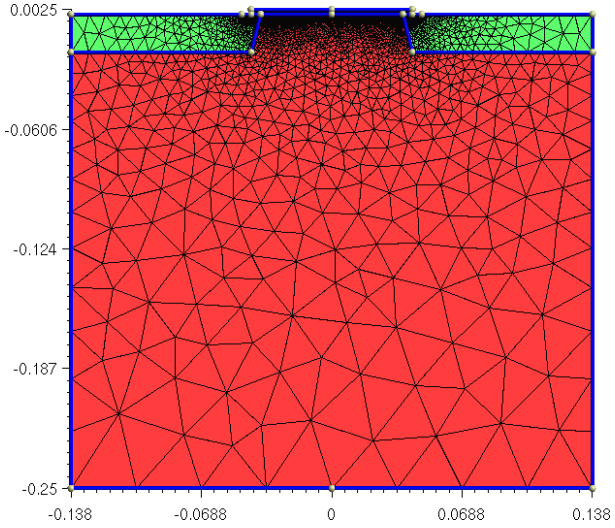

Figure 3.2: 2D Mesh for the mosfet device obtained with GMSH

1 - Definition of Device Regions

Three TiberCAD regions are defined: to each of them, one mesh_region is associated, that is the Phisical Surfaces **1, 2** and **3** defined in Step 1. However, in general more than one mesh_region can be associate to a single TiberCAD region, if this is convenient.

```
Region substrate
  {
    mesh_regions = 1
    material = Si
    doping = 1e18 doping_type = acceptor
  }

  Region contact
  {
    mesh_regions = 2
    material = Si
    doping = 5e19 doping_type = donor
  }

  Region oxide
  {
    mesh_regions = 3
    material = SiO2

  }
```

2 - Definition of Simulation

Now we define the **Simulation** *dd*: it belongs to the class **driftdiffusion**

```
  model driftdiffusion
 {

   options
   {
    simulation_name = dd
    physical_regions = all
   }
```

We declare two **driftdiffusion physical models**: the first defines a *srh* **recombination** model (see 6.3.1); the second defines a *field-dependent* **mobility** model for electrons which implements a *doping dependence* for the **low-field mobility** (see 6.3.3).

```
physical_model recombination
{
  model = srh
}

physical_model electron_mobility
{

  model = field_dependent
  low_field_model = doping_dependent

}
```

3 - Definition of Boundary Conditions

The source, drain and gate contacts of the Mosfet device are defined as **Boundary conditions regions** (*BC_Region source , BC_Region drain, BC_Region gate*) in the following way:

```
BC_Region gate
  {
    BC_reg_numb = 2
    type = schottk
    barrier_height = 3.0
    voltage = @Vg[0.0]
  }

  BC_Region source
  {
    BC_reg_numb = 1
    type = ohmic
```

```
    voltage = 0.0
  }

  BC_Region drain
  {
    BC_reg_numb = 3
    type = ohmic
    voltage = @Vd[0.5]
  }
```

To each of the **BC regions**, one *BC_reg_numb* is assigned, that is one of the Physical Lines **1,2, 3** defined in **Step 1**, which represent the contact regions.

Note that, while *source* and *drain* are defined as *type= ohmic*, *gate* **BC region** is defined as *type = schottky*; *barrier_height = 3.0* specifes the metal/oxide interface barrier and depends on the contact metal workfunction.

Drain voltage is defined as *@Vd[0.5]* and gate voltage as *@Vg[0.0]*. This specifies that the value of the voltage will be determined at each moment of the simulation, by the value of the two variables *Vd* and *Vg*, which will be assigned in the **sweep** definition.

4 - Definition of Simulation parameters

Two sweeps are requested for this simulation, that is an external loop on *Vg* (the gate voltage) and an internal loop on *Vd* (the drain voltage) for each value of *Vg*; in this way, the IV drain characteristics for a series of gate biases are obtained in output.

```
   sweep_1
 {
   simulation = dd
   variable = Vd
   start = 0.0
   stop = 2.0 #0.1
   steps = 200  #200 #1
#   plot_data = true
 }

 sweep_2
 {
   variable = Vg
```

```
    start = -0.1
    stop = 0.5
    steps = 6
    simulation = sweep_1
    #simulation = driftdiffusion
  }
```

5 - Definition of Execution parameters

In the **Simulation** section , we decide the simulation dimension (*dimension = 2*), then *which* simulations to perform and in which *order*; we set *solve = sweep_2*, to execute the external gate voltage sweep *sweep_2* which in its turn call the sweep *sweep_1* where drain current is calculated for all the chosen drain voltage steps by running *dd* **simulation**.

```
$Simulation
{
   meshfile = mosfet.msh
  dimension = 2
  temperature = 300
  solve = sweep_2
  resultpath = output_IV_char
  output_format = vtk
  plot = (Ec, Ev, QFermi_e, QFermi_h, eDensity, hDensity, eCurrent, hCurrent,
          NetRecombination, EField, ElPotential, ContactCurrents)
}
```

Output files with conduction and valence band profiles, quasi-fermi levels, electron and hole density, recombination, electric field and potential (*plot = Ec,Ev,.....*) will be generated, together (*ContactCurrents*) with a file with all the calculated values of the drain current at the contacts for each gate bias step (the IV characteristics).

Step 4: Run TiberCAD

Now we can run TiberCAD:

```
tibercad mosfet.tib
```

The generated **Output** files are:

driftdiffusion_materials.vtk: information about the material regions of the device.

driftdiffusion_nodal.vtk output for the nodal quantities which have been calculated, e.g. conduction and valence bands, (quasi)fermi levels, electron and hole density and mobility.

driftdiffusion_elemental.vtk output for the elemental quantities (e.g. electric field, current density).

sweep_2_driftdiffusion_Vg_0.000_Vd.dat and similar for all the Vg steps: drain current characteristics for each Vg bias.

Chapter 4

Input for TiberCAD

Input for TiberCAD is composed by an input file e.g. "input.tib" and a mesh file generated by a mesher software: as for now, mesh files from GMSH (*.msh, v.1 and v.2.0) and from ISE-TCAD (*.grd) are supported.

Be sure that the material files are in the correct directory (as specified in 4.7).

To run the program, type: **tibercad** *input_file_name*

4.1 Description of Input file structure

A valid input file for TiberCAD is a text file with the structure described in the following.

In the whole input file, everything following a '#' is considered as a comment and is disregarded; blank lines can be present anywhere and are disregarded too.

Input file is composed by several **sections**: each **section** begins with a **section-name** preceded by **"$"** (e.g. $Physics).

A section is enclosed between **"{"** and **"}"** brackets and is possibly composed (depending on the section) by a variable number of **blocks** enclosed between "{" and "}" brackets.

Each **block** can be possibly composed by one or more blocks, each preceded by a block-name.

The elementary block (**parameters-block**) is a block which contain zero or any number of **parameter assignements** in the form:

"*tagname* = *tagvalue*",

where

- "*tagname*" is a string
- "*tagvalue*" is a single numerical or string item or a list of items between "(" and ")" parenthesis and separated by commas. e.g. *(cathode, anode)*

Format is free for the parameter assignements, provided that they are separated by spaces. Everything which follows a '#' is considered as a comment and is disregarded.

For example:

```
driftdiffusion
  {
    coupling = poisson
    nonlin_max_it = 70
    nonlin_rel_tol = 1e-10

    ls_max_step = 2
    #ls_type = none
    discretization = fem
    integration_order = 2
    #pc_type = composite
    ksp_type = bcgs
    #quasi_equilibrium = (cathode, anode)
  }
```

Here and in the whole input file a string item can include a combination of characters, special characters and numbers, but not spaces; if a space is found , the string item is taken as terminated.

The input file is composed by the following sections:
Geometry, **Device** , **Scale**, **Models** , **Physics**, **Solver**, **Simulation**
which will be described in the following.

4.2 Device section

```
$Device
{
 Region buffer
   {
   .........
   }
 Region barrier_1
   {
     ............
   }
   ................
```

```
}
```

In "**Device**" section, two kinds of block can be present: the **Region** blocks contain the description of the device in continuous media approach; each of the **Cluster** blocks define a group of regions (mesh_regions) even with different physical properties, but to be treated together somewhere in the simulation (e.g. quantum calculation). In this way it is possible to refer to the set of these regions simply by the **Cluster** name.

Each **Region** block must be preceded by the keyword "**Region**", followed by the (single-word) name of the **TiberCAD Region**. For an ISE-TCAD mesh, it can be the name of an ISE-TCAD mesh region, as defined during the modeling of the device; in this case, if *mesh_regions* is absent, the **TiberCAD Region** will be associated to that ISE-TCAD mesh region.

```
Region QWell
{
  mesh_regions  = (4,5)
  # mesh_regions  = 4
  structure = wz
  y-growth-direction = (1,0,-1,0)
  z-growth-direction = (-1,2,-1,0)
  x-growth-direction = (0,0,0,1)
  material = GaN
  doping = 1e17 doping_type = donor doping_level = 0.025
}
```

Here are the description of the available keywords for a **Region** block.

material (mandatory) : name of the material associated to the present region; it can be an alloy, in this case the keyword x must be present.

x : alloy concentration; e.g. in $Al_xGa_{1-x}As$, x is Al concentration

mesh_regions : (a list of) region ID(s) (for GMSH) as specified in the meshing program , or ISE-TCAD name(s) (to be implemented). If it is not present, the **TiberCAD Region** name must be a valid name of an ISE-TCAD mesh region.

structure : crystal structure (wz = wurtzite, zb = zincblend)

x-growth-direction, *y-growth-direction*, *z-growth-direction*: Bravais vectors with Miller indexes for wurtzite crystal (4 element vectors) or zincblende crystal (3 element vectors).

doping : doping concentration [cm^{-3}]

doping_type : donor or acceptor

doping_level: energy level of the dopant [eV]

Each **Cluster** block must be preceded by the keyword "**Cluster**", followed by the (single-word) name of the **Cluster**.

```
Cluster  Quantum_1
  {
    mesh_regions    = (3,4, 5)
  }
```

mesh_regions (mandatory): list of the physical regions (region ID(s) (for GMSH) as specified in the meshing program , or ISE-TCAD name(s)) to be grouped in the cluster.

Regions and **Clusters** represent the macroscopical description of the device or structure to be be simulated in **TiberCAD**. In the rest of the input file, the physical regions associated to **Models** or **Atomistic** descriptions will be indicated by means of the **TiberCAD Region** and **Cluster** names.

4.3 Scale section

The section "**Scale**" is dedicated to the optional definition of Non-Continuous Media regions for the device: these regions wiil be described and studied at a different scale (e.g. atomistic, circuit level lumped model, etc.) As for now, just the atomistic description is implemented. **Atomistic** blocks, if present, specify a possible atomistic description associated to one or to a group of physical regions described by **Region** blocks. So, for each **Atomistic** block defined in Input file, an atomic structure description will be generated and used to solve a simulation problem with an atomistic approach. The association to the physical (macroscopic) regions of the device allows the implementation of multi-scale calculations.

Each **Atomistic** block must be preceded by the keyword "**Atomistic**", followed by the (single-word) name of the atomistic region.

```
Atomistic  TB_1
 {
    physical_regions = ( barrier_1, qwell, barrier_2)
            # physical  regions to be described
                                    # with atomistic model.
 }
```

Here are the description of the available keywords for an **Atomistic** block.

physical_regions (mandatory): list of the physical regions (**TiberCAD Regions** or **Clusters**) of the device associated to an atomistic description. *all* (default) is used to specify all the physical regions.

path (optional): path for importing an atomistic structure from an external file. *xyz* and *gen* formats are supported, and are automatically recognized by file extension. Each of the atom positions is imported as is, so the atom coordinates must be consistent with the geometry of the device.

If no path is specified, the **TiberCAD Atomistic Generator** builds the atomistic structure; it is constructed as a bulk crystal structure, covering with proper atomic species the physical regions and taking in account the dimension of the problem (up to now 1D structures are supported).....

Atomistic Generator options, to be put in the Atomistic section, are described in the following.

reference_region (mandatory): the Atomistic Generator can only build pseudomorphical heterostructures. A reference region must be defined to specify from which region (**TiberCAD Regions**) to get structure parameters such as lattice constants, which depend on the material defined in the reference region.

passivation (optional): *no* is default option. If set to *no*, no passivation is performed. If *yes* is specified, a hydrogenation of the structure is performed, taking into account the structure periodicity. Up to now, hydrogenation is supported fo Silicon structures. .

preserve (optional): Default is *none*. In some cases it is requested to build a structure in which the atom basis or the conventional cell has be preserved, regardless to mesh geometry. If *none* is specified, no conservation is performed and only atoms strictly belonging to geometrical regions are put in the atomic structure. If *lattice* is specified, atom basis is preserved (e.g. to preserve anion/cation couples). If *conventional* is specified, conventional cell is preserved. .....

y_lenght (optional): Atomistic Generator builds the minimum periodical structure along y and z directions. If y_lenght is specified, the structure will be at least y_lenght sized along y_growth_direction. Exact lenght is internally defined in order to keep structure periodicity.

z_lenght (optional): same as above, for the z direction.

4.4 Models section

```
$Models
{
 model driftdiffusion
  {
   ..........
   BC_Regions
    {
      BC_Region cathode
```

```
      {
       ............
      }
      BC_Region anode
      {
        ..............
      }
    }
  }
 model macrostrain
  {
  ..........................
```

In "**Models**" section, one or more model-blocks must be present: each model-block must be preceded by the keyword "**model**", followed by the (single-word) model name. This must be the name of one of the TiberCAD simulation models.

Here are the simulation models implemented until now:

- **driftdiffusion**: Poisson-driftdiffusion transport of electrons and holes
- **thermal**: Heat balance simulation
- **excitontransport**: Exciton transport model
- **macrostrain**: Calculation of Elastic deformations in heterostructures
- **efaschroedinger**: Envelop Function Approximation (EFA) solution of single-particle Schrödinger equation for electrons and holes
- **quantumdensity**: Calculation of quantum density of electrons and holes.
- **quantumdispersion**: Dispersion of quantized states in **k** space
- **opticskp**: Optical properties (optical kp matrix elements)
- **opticalspectrum**: Emission spectrum (with **k**-space integration)

For a complete description of these simulation models, see the next chapters.

Each model-block can contain some optional blocks, to be written in the following order:

- one "'options"' block, preceded by the keyword "**options**". This block can contain general options for the present model.

- one or more **physical_model** blocks: each physical_model block must be preceded by the keyword "**physical_model**", followed by the (single-word) name of the physical model. Each physical_model block can contain parameters relevant to a specifical model of a physical property or quantity related to the present model.

- one or more Boundary Condition regions blocks (**BC_regions**-block). The BC_-regions-block must be preceded by the keyword "**BC_Regions**" and it is composed by one or more parameters-blocks, each preceded by the keyword "**BC_-Region**" followed by the (single-word) name of the boundary condition region. This parameters-block can contain the possible description of the boundary region.

These optional blocks must be strictly in this order: first the **options**, then the **physical_model**, and finally the **BC_regions**-blocks. A detailed description of the possible parameters for these blocks follows.

4.4.1 options block

```
options
    {
     simulation_name = driftdiffusion
     #physical_regions = all
     physical_regions = (channel_1 , channel_2)
    }
```

simulation_name: user-defined name of the particular instance of the simulation model defined for this block. More than one simulation (with different name and properties) can be defined,in separated model blocks, which refer to a same TiberCAD simulation model. If simulation_name is not assigned, by default the TiberCAD model name is taken as current simulation_name.

physical_regions: (list of) physical region(s) to which the present simulation model will be applied. Physical region(s) are the **TiberCAD regions** or **clusters** as defined in **Device** section

Default value is "'all"' (all physical regions of the device). In a list, the names must be separated by comma and enclosed between '(' and ')' parenthesis

4.4.2 physical_model block

```
    physical_model recombination
    {
      model = SRH
    }
```

Currently available physical_models and parameters:
recombination:
model: SRH,direct, exciton_generation, exciton_dissociation
exciton_simulation: excitons
electron_mobility
model: doping_dependent
hole_mobility
model: doping_dependent

4.4.3 BC_region block

```
BC_Region anode
     {
       BC_reg_numb = 2
       type = ohmic
       #voltage = 0.0
       voltage = @Vb[1.5]
     }
```

BC_region: name of the present boundary region
BC_reg_numb: BC region ID(s) as specified in the meshing program (GMSH).
type: type of boundary condition: ohmic, schottky,... , substrate (for strain calculations).
voltage: value of voltage [V] applied to the present BC region (for ohmic and schottky BCs); it can be the value of a sweep variable 'Vb', indicated with @Vb. A possible default value can be indicated in parenthesis: @Vb[1.5]
zero_grad_fermi_h, *zero_grad_fermi_e*: if true set Neumann b.c. to the fermi level in the b.c. region.
If *type* is *substrate* (for **strain** calculations):
material : name of material in the *substrate* region.
structure : crystal structure (wz = wurtzite, zb = zincblend)
x-growth-direction, *y-growth-direction*, *z-growth-direction*: Bravais vectors with Miller indexes for wurtzite.

4.5 Solver section

```
$Solver
{
driftdiffusion
```

```
  {

    nonlinear_solver = tiber

    ksp_type = bcgsl
    nonlin_rel_tol = 1e-12
    nonlin_abs_tol = 1e-15
    nonlin_step_tol = 1e-2
    #nonlin_rel_tol = 1e-12
    lin_rel_tol = 1e-6
    nonlin_max_it = 30
    #local_density_scaling = true
    #ls_type = none
    discretization = fem
    ls_max_step = 1
    #pc_type = lu
    pc_type = composite
    integration_order = 2
    #relaxation_factor = 0.5
  }

..................
```

In this section one can define the setting parameters for the numerical solvers: the section is organized in blocks, each one preceded by a block-name equal to one of the user-defined simulation name. Solver parameters defined in each block refer to that particular simulation.

Two extra blocks can be present:

- **sweep** block, preceded by the keyword "**sweep**". This block contains the setting for a set of calculations applied to a boundary region (e.g. to a drain contact for the calculation of a IV characteristic).

```
sweep
  {
    simulation = driftdiffusion
    variable = Vb
    start = 0.0
    stop = 4.0
```

```
    steps = 80
    plot_data = true
    plotvariable = current
  }
```

variable : name of the variable to which sweep is applied: its value is assigned to a quantity (e.g. voltage) in a BC Region section.

start , **stop**, **steps**: sweep starts from *start* value, is repeated *steps* times and stops in *stop*

simulation : name of the simulation (model) associated to the sweep calculation.

plotvariable : specify the integrated quantity to be calculated during the sweep and that will be shown in the output file sweep_*modelname_sweepvariable*.dat, eg. sweep_driftdiffusion_Vb.dat for a sweep of current calculation on the variable *Vb* (typically a contact voltage)

plot_data : default is *false*; if it is set to *true* output data will be written for each step of the sweep calculation, otherwise just the results for the final step will be present in the output.

- **selfconsistent** block , preceded by the keyword "**selfconsistent** ". In this block it is possible to define a self-consistent calculation based on two different simulation models (e.g. driftdiffusion and excitontransport).

```
selfconsistent
  {
    flavour = relaxation
    simulations = (driftdiffusion,  excitons)
  }
```

In **simulations** the list of simulations to be performed self-consistently is specified.

Now it is possible to execute the specified simulations in self consistent way, by using the **selfconsistent** keyword like a simulation name, in the **solve** assignement, e.g. *solve = selfconsistent* , or even in the **sweep** section, with, for example, *simulation = selfconsistent*.

4.6 Physics section

In this section several physical parameters can be entered, in addition to or overwriting the material parameters present in the material files. The section is organized in blocks,

each one preceded by a block-name equal to one of the user-defined simulation name. Physical parameters defined in each block refer to that particular simulation.

```
driftdiffusion
  {
    model = unstrained
  }
```

For example in this case:

model: specification of generical drift-diffusion or exciton transport simulation. Possible values: *simple*; *strained*: effects of strain (deformation potentials, piezo and pyro polarization fields) are taken in account ; *unstrained*: effects of strain are NOT taken in account (even if strain calculation is being performed !).

4.7 Simulation section

In this section one can specify several general parameters and settings for the actual calculation to be run, such as the mesh file to be used, the dimension of simulation, the process-flow of simulation, etc.

searchpath : path for material files

meshfile : name of mesh file. N.B.: the extension is mandatory! (*.grd* for ISE-TCAD, *.msh* for GMSH mesh file v.1 and v.2.0)

mesh_units : units of measurements used in the meshing (relative to meters): e.g., 10^{-6} for μm

dimension : dimension of simulation (1,2,3)

temperature : temperature of the system

solve : list of simulations to be executed, in the order of execution; if the list contains "'sweep"', a sweep is performed as specified in *sweep* block in the *Solver* section.

```
solve =  (strain,driftdiffusion, quantum_electrons, quantum_holes)
```

resultpath : path for output directory

output_format : format of the output data: *gmv* for **GMV** , *ise* for **Tecplot** , *grace* for **xmgr** (ascii data column type), *vtk* for **Paraview**.

plot : list of output variables which are calculated and available in output files. See the corresponding chapters for the available output variables for each model.

4.8 Output description

At the end of the execution, the program will write the results of the simulation in the directory specified by *resultpath* , with the format specified by *output_format*. The output variables are specified in the list *plot*.

TiberCAD output is divided in three classes: **nodal**, **elemental** and **integrated** quantities.

Nodal quantities are all the quantities associated with the nodes of the mesh, such as Fermi level, electron and hole density, conduction and valence band, etc.. The output values for these quantities are reported in the files *modelname*_nodal.*ext* , where *modelname* is the simulation model used for the calculations and *ext* is the extension of the chosen file format.

In the case a sweep calculation is performed and the **plot_data** keyword is set to *true*, the output files are of the kind *modelname*_nodal_*sweepvariable_step.ext*, where *sweepvariable* is the variable with respect to which the sweep is performed (e.g. gate voltage) and *step* is the value of this variable at that step; e.g *driftdiffusion_nodal_Vb_0.000.dat* for the result at the step Vb = 0.0 .

Elemental quantities are all the quantities associated with the elements of the mesh, such as current density. The output values for these quantities are reported in the files *modelname*_elemental.*ext* .

In the case a sweep calculation is performed and the **plot_data** keyword is set to *true*, the output files are of the kind *modelname*_elemental_*sweepvariable_step.ext*. e.g. *driftdiffusion_elemental_Vb_1.150.dat*

Integrated quantities are the quantities which are not associated to the mesh but are obtained by an integration on real or reciprocal space, for example current at the contacts of a diode or quantized energy levels in a quantum well. These **Integrated** quantities are displayed in separated files, with the format *simname.ext*, e.g *quantum_electrons.dat*, where *simname* is the name of the model (simulation) associated to the results. If a sweep is performed, the output file gets the format sweep_*simname_varname.ext*, where *varname* is the variable with respect to which the sweep is performed, for example *sweep_driftdiffusion_Vb.dat*. Inside the file, output values for all the steps of calculation are shown.

Finally, a last class of output files is the **Materials** output. These files contain the information about the physical regions of the device; for each class of simulation, a different material file is produced, containing all and only the mesh regions associated to that simulation model. The file has the format *simulationname*_materials.*ext*, e.g. *driftdiffusion_materials.dat*

4.9 Example of Input file

Here is an example of the input file template:

```
# Description of  the  device physical regions
$Device
{

# Syntax:
#
# Region  "Tiber_region"
# mesh_regions    = "list gmsh reg ID" | "list ISE_TCAD reg names"
#
#if  mesh_regions is empty ->  mesh_regions = "Tiber_region"
#

 Region buffer
   {
     mesh_regions  = 1
     structure = wz
     y-growth-direction = (1,0,-1,0)
     z-growth-direction = (-1,2,-1,0)
     x-growth-direction = (0,0,0,1)
     material = GaN
     doping = 1e15
     doping_type = donor
     #doping_level = 0.025
   }



 Region barrier_1
   {
     mesh_regions    = (2,3)
     structure = wz
     y-growth-direction = (1,0,-1,0)
     z-growth-direction = (-1,2,-1,0)
```

```
    x-growth-direction = (0,0,0,1)
    material = AlInN
    x =     0.80 #
    doping = 1e15
    doping_type = donor
    #doping_level = 0.025
  }



Region QWell
  {
    mesh_regions  = 4
    structure = wz
    y-growth-direction = (1,0,-1,0)
    z-growth-direction = (-1,2,-1,0)
    x-growth-direction = (0,0,0,1)
    material = GaN
    doping = 1e15 #
    doping_type = donor #
    # doping_level = 0.025
  }


Region barrier_2
  {
    mesh_regions    = (5,6)
    structure = wz
    y-growth-direction = (1,0,-1,0)
    z-growth-direction = (-1,2,-1,0)
    x-growth-direction = (0,0,0,1)
    material = AlInN
    x =   0.80 #
    doping = 1e15 #
    doping_type = donor
    # doping_level = 0.025
  }
```

```
# Cluster = group of  mesh_regions with DIFFERENT  material (in general)

# Syntax:
#
# Cluster  "Tiber_cluster"
# mesh_regions    = "list gmsh reg ID" | "list ISE_TCAD reg names"
#
#  "Tiber_cluster" to be used in Models section

   Cluster  Quantum_1

   {

     mesh_regions    = (3,4, 5)

   }


}


#Definition of  the description scale (only for not-Continuous Media regions  )
# Syntax:
#
# "level"  "scale_cluster"
# "level" = "Atomistic | ..."
# physical_regions =  "list (Tiber_region | Tiber_cluster) "
#
#*******  $Scale section is  optional *********
#

$Scale
{


  Atomistic  TB_1

  {

    physical_regions =  (barrier_1 , QWell  ,  barrier_2 )
```

```
  }

  Atomistic  TB_2

  {

    physical_regions =  ..........

  }

}

# Definition of  Simulation Models  and associated Boundary Conditions
$Models
{

 model driftdiffusion
  {

    options
    {
     simulation_name = driftdiffusion

     physical_regions = all
    }

    physical_model recombination
    {
      model = srh
    }

    physical_model recombination
    {
      model = direct
```

```
      C = 1.1e-8
    }


    BC_Regions
    {
      BC_Region cathode
      {
        BC_reg_numb = 1
        type = ohmic

        voltage = 0.0
      }


      BC_Region anode
      {
        BC_reg_numb = 2
        type = ohmic

voltage = 0.0
      }



    }


 }


 model macrostrain
  {
    options
    {
      simulation_name = strain
      physical_regions = all
    }

    BC_Regions
```

```
    {
      BC_Region substr
      {
        BC_reg_numb = 1
type = substrate
        material = GaN
structure = wz
        y-growth-direction = (1,0,-1,0)
        z-growth-direction = (-1,2,-1,0)
        x-growth-direction = (0,0,0,1)
      }
    }
  }


  model efaschroedinger

  {


    options
    {
      simulation_name = quantum_electrons

# Syntax:
#
# physical_regions =  "list (Tiber_region | Tiber_cluster) "

      physical_regions = Quantum_1

    }


  }

 model efaschroedinger

  {

    options
```

```
    {
     simulation_name = quantum_holes
     physical_regions = Quantum_1

    }

  }


}


# Definition of  Model-dependent Solver parameters
$Solver
{



driftdiffusion
  {
    coupling = poisson
    ksp_type = bcgsl
    nonlin_abs_tol = 1e-10
    nonlin_step_tol = 1e-2
    #nonlin_rel_tol = 1e-12
    lin_rel_tol = 1e-6
    nonlin_max_it = 30
    #local_density_scaling = true
    #ls_type = none
    discretization = fem
    ls_max_step = 1
    #pc_type = lu
    pc_type = composite
    integration_order = 2
    #relaxation_factor = 0.5
  }



 macrostrain
```

```
  {
    substrate = substr
  }

  efaschroedinger
  {
    x-periodicity = false
    Dirichlet_bc_everywhere = true
#   particle = hl
    number_of_eigenstates = 30
 #   model = conduction_band  #eff mass  cb
    poisson_model_name = driftdiffusion  #  potential from driftdiffusion
    strain_model_name = macrostrain
    convergent_density = true
  }

 quantum_electrons
  {
    particle = el

  }

 quantum_holes
  {
    particle = hl

  }


}



# Definition of  Model dependent physical parameters
$Physics
{

  driftdiffusion
  {
    statistics = FD
```

```
    strain_simulation = macrostrain  #  default driftdiffusion model including
     # local strain  obtained from "macrostrain"

  }

 quantum_electrons
  {
    particle = el
    model = conduction_band   #eff mass  cb
  }

  quantum_holes
  {
    particle = hl
    model = kp   #  k.p  for  valence  band
    kp_model = 6x6

  }




}



# Definition of  model-indipendent parameters of the Simulation

$Simulation
{

 searchpath = ../../materials

 mesh_units = 1e-9       #nm !!
 dimension = 1
 meshfile = test.msh
 temperature = 300
  solve =  (strain, driftdiffusion, quantum_electrons,quantum_holes )
```

```
   resultpath =  output_

  plot = (Ec, Ev, QFermi_e, QFermi_h, EField ,
          eDensity, hDensity, eCurrent, hCurrent,
          Current, NetRecombination, eMob, hMob, T,
            strain, polarization, xEffPot, xDensity,
          xMob, ExcitonRecombination, EigenFunctions,
          EigenEnergy,EnergyLevels,   xCurrent)

  output_format = grace

}
```

Chapter 5

Simulation of strain

5.1 Theory

The theoretical model of strain simulation can be found in Refs.[1, 2]. The code can compute elastic deformations in a heterostructure and can calculate the deformed shape of the structure. The heterostructure can be either grown on a substrate or not. External pressure may be applied to a structure as well.

5.2 Models section parameters

The **Models** section looks like follows:

```
model macrostrain
{
    options
    {
         simulation_name = strain_in_transistor
         physical_regions = (2, 3, 4)
    }
 }
```

There are three possible kinds of boundary conditions. The mandatory keyword
type = { substrate | pressure | extended_material}
specifies the boundary condition type.

5.2.1 Substrate boundary condition

In this case the boundary condition region is the boundary between the device and the substrate. The substrate does not belong to the device. Therefore it is necessary to

define both the boundary region number and the substrate material

Role of substrate. *In general, the "substrate" is a material that defines the lattice matching conditions, and not necessarily a real solid body on which the device is grown.*

```
BC_Region layer_of_Al_0.3_Ga_0.7_N
{
     BC_reg_numb = 14
     type = substrate
     mat = AlGaN
     x = 0.3
     structure = wz
     y-growth-direction = (1,0,-1,0)
     z-growth-direction = (-1,2,-1,0)
     x-growth-direction = (0,0,0,1)
}
```

5.2.2 External pressure boundary condition

The parameter *pressure* specifies the value (in GPa) of the normal pressure applied to the boundary region *BC_reg_numb*.

```
BC_Region tip_upon_a_surface
{
     BC_reg_numb = 12
     type = pressure
     pressure = 12.3
}
```

Sign of pressure. *The value of the pressure has a positive sign if the external force acts towards the surface, which in general has to be the boundary of a simulation environment.*

5.2.3 Extended device boundary condition

If device that is grown on a substrate is very large we may want to simulate a part of it only. In this case the simulation domain boundary is not a free surface any more. The boundary conditions are as follows:

$$\int C_{ijkl} \frac{\partial u_k}{\partial x_k} n_i d\partial\Omega = 0 \tag{5.1}$$

The syntax is as follows:

```
BC_Region boundary1
{
   BC_reg_numb = 12
   type = extended_material
}
```

5.3 Solver parameters

The choice of the necessary parameters to be put in the **Solver** section depends on the type of the strain boundary condition for the structure, namely, if it is considered as grown on a substrate or not.

5.3.1 Structure with a substrate

The only mandatory parameter is *substrate*, to which a name of a substrate boundary condition region has to be assigned, e.g (referring to the previous example):

```
strain_in_transistor
{
   substrate = layer_of_Al_0.3_Ga_0.7_N
}
```

5.3.2 Structure without a substrate (freestanding)

In this case, the parameter *substrate* should not be present; instead, the following parameters should be defined.

- The reference lattice material is defined by the coordinates of a point belonging to this material, using the parameter *reference_material_point*.
- As follows from Ref. [1], additional geometrical points have to be specified, according to the device dimensionality. The corresponding parameters are: *fixed_point1*, *fixed_point2* and *fixed_point3*.

Since the elasticity energy is invariant with respect to translations and rotations of the structure, then, for the sake of uniqueness of solutions of the equations, another set of constraints is required. Hereafter we assume that a mesh is defined over the simulation domain and the displacement field $\mathbf{u}(\mathbf{r})$ is defined at the mesh nodes.

Let $\mathcal{D}$ be the dimensionality of the structure minus the number of directions along which the structure is periodic. If $\mathcal{D} > 0$, then a Dirichlet boundary condition is applied at an arbitrarily chosen node i_1:

$$\mathbf{u}(\mathbf{r}_{i_1}) = \mathbf{0}, \tag{5.2}$$

in order to prevent the structure from undesirable translations. In the case of $\mathcal{D} > 1$, another node i_2 is chosen and a constraint

$$(\mathbf{u}(\mathbf{r}_{i_1}) - \mathbf{u}(\mathbf{r}_{i_2})) \cdot (\mathbf{r}_{i_1} - \mathbf{r}_{i_2}) = 0 \tag{5.3}$$

is applied, in order to keep the direction between the nodes i_1, i_2 unchanged. If $\mathcal{D} = 3$, another node i_3 is chosen and additional constraint is set:

$$(\mathbf{r}_{i_1} - \mathbf{r}_{i_2}, \mathbf{r}_{i_1} - \mathbf{r}_{i_3}, \mathbf{u}_{i_3}) = 0, \tag{5.4}$$

so the node i_3 has to belong to the $(\mathbf{r}_{i_1}, \mathbf{r}_{i_2}, \mathbf{r}_{i_3})$ plane.

Example for a 2D simulation:

```
 strain_in_transistor
{
  reference_material_point  = (0, 100, 0)
  fixed_point1 = (0, 0, 0)
  fixed_point2 = (10, 0, 0)
}
```

5.3.3 Additional parameters

Numercal solver parameters

tolerance: relative tolerance of the iterative solver, e.g.

```
 tolerance = 1e-10
```

The default value is 1e-10.

ksp_type = type of solver: **gmres**, **bcgsl**, **bcgs**, **cg**, **richardson**.

Default is:

- **gmres** for 1D
- **bcgsl** for 2D and 3D

pc = type of pre-conditioner : **ilu**, **composite**, **jacobi**, **lu**, **cholesky**, **eisenstat**.
Default is :

- **ilu** for 1D
- **jacobi** for 2D and 3D

max_iterations = max number of iterations (default = 1000)

monitor, *xmonitor*: if **true**, textual or graphical monitor of convergence process is enabled (default = **false**)

Periodic boundary conditions

It is possible to specify periodic boundary conditions along the coordinate axes. The relative parameters are:

periodicity_x = { true | false }
periodicity_y = { true | false }
periodicity_z = { true | false }
The default value is **false**.

Mesh refinement

For the details about mesh refinement refer to the Libmesh library documentation. The parameter *refinement_steps* defines the number of the refinement steps to be done (with default value equal to zero). The parameter *uniform_refinement* = { true | false } is used to choose between uniform and adaptive refinement. The default value is **false**, i.e. adaptive refinement. Example:

```
refinement_steps = 4
refine_fraction = 0.25
coarsen_fraction = 0
max_refinement_level = 10
```

Deformed shape calculation

The displacement field and lattice matching parameters that are found from master equations can be used in order to define a new shape of the heterostructure. This new shape is the first approximation to the equilibrium one. The next approximations are obtained iteratively by the following steps: at the n-th iteration the master equations are solved using the lattice matching deformation ε_{ij}^n which is defined as

$$\varepsilon_{ij}^n = \frac{1}{2}\left(\frac{\partial u_i^{n-1}}{\partial x_j} + \frac{\partial u_j^{n-1}}{\partial x_i}\right) + \varepsilon_{ij}^{n-1}, \tag{5.5}$$

where the displacement field $\mathbf{u}^{n-1}$ has been taken from the iteration $n-1$. Then the new shape is defined by using the displacements from the last step solution, and the iterative process is repeated until the displacement field vanishes and additional lattice parameters stabilise. The iterative cycle usually converges after 3 - 4 iterations.

The only parameter that controls shape calculation is *number_shape_steps*. The value defines number of iterations. The default value is zero, that means no shape deformation calculation.

5.4 Physics section parameters

There is a possibility to consider converse piezoelectric effect. For this it is necessary to specify a name of another simulation that can provide electric field. The parameter is *poisson_equation*. Example:

```
macrostrain
{
   poisson_equation = DriftDiffusion
}
```

Interaction with other simulations. *In order to take into account the converse piezzo effect, the poisson equation has to recalculate the necessary parameters after the strain simulation. To do so, the following parameters has to be set in the Physics section of the drift-diffusion equation (for detailes see Sec. 6.4):*

```
driftdiffusion
{
    model = strained
    strain_simulation = str
    recompute_band_parameters = true
}
```

5.5 Output

The output variables are:

- **strain** strain tensor (6 components) in calculation system
- **polarization** piezo polarization vector (3 components) in calculation system

Chapter 6

Drift-diffusion simulation of electrons and holes

6.1 Theory

The semi-classical transport simulation of electrons and holes is based on the drift-diffusion approximation (see e.g. [3]).

Beside the electric potential the electro-chemical potentials are used as variables such that the system of PDEs to be solved reads as follows

$$\begin{aligned} -\nabla(\varepsilon\nabla\varphi - \mathbf{P}) &= -e(n - p - N_d^+ + N_a^-) \\ -\nabla(\mu_n n(\nabla\phi_n + P_n\nabla T)) &= R \\ -\nabla(\mu_p p(\nabla\phi_p + P_p\nabla T)) &= -R \end{aligned} \tag{6.1}$$

P is the electric polarization due to e.g. piezoelectric effects and R is the net recombination rate, i.e. recombination rate minus generation rate. P_n and P_p are the electron and hole thermoelectric power, respectively. The models for the mobilities and the net recombination rates can be specified in the `physical_model` sections as described in the following.

6.2 Plot variables

See tables 6.1, 6.2 and 6.3.

6.3 `Models` section

The `Models` section looks as given in Listing 1

```
model driftdiffusion
{
    options
    {
         simulation_name = whatever_you_want
         physical_regions = (2, 3, 4)
    }

    physical_model recombination
    {
      model = model_to_be_used
      ...
    }

    physical_model electron_mobility
    {
      model = model_to_be_used
    }

    physical_model hole_mobility
    {
      model = model_to_be_used
    }

    physical_model thermoelectric_power
    {
      model = model_to_be_used
    }

 }
```

Listing 1: `Models` section for drift-diffusion

Nodal quantities		
Ec	Conduction band edge	eV
Ec0	Conduction band edge	eV
Ev	Valence band edge without electric potential	eV
Ev0	Valence band edge without electric potential	eV
Eg	Band gap	eV
QFermi_e	Electro-chemical potential of electrons	eV $(-e\phi_n)$
QFermi_h	Electro-chemical potential of holes	eV $(-e\phi_p)$
ElPotential	Electric potential	V
eDensity	Electron density	cm^{-3}
hDensity	Hole density	cm^{-3}
eMob	Electron mobility	$\mathrm{cm}^2V^{-1}s^{-1}$
hMob	Hole mobility	$\mathrm{cm}^2V^{-1}s^{-1}$
Nd	Ionized donor density	cm^{-3}
Na	Ionized acceptor density	cm^{-3}
charge_density	Total charge density	cm^{-3}
Pn	Electron thermoelectric power	V K^{-1}
Pp	Hole thermoelectric power	V K^{-1}
NetRecombination	The net recombination rate for each recombination model and the total rate	$\mathrm{cm}^{-3}\mathrm{s}^{-1}$

Table 6.1: Nodal quantities

The physical_model sections can be omitted. In this case default models are used, namely no recombination/generation for the recombination model and constant mobility for the mobility models. There can be more than one recombination model.

6.3.1 Recombination models

This section describes the currently available generation/recombination models.

Shockley-Read-Hall (SRH) recombination

The SRH recombination model can be enabled in the input file as shown in Listing 2

SRH recombination is defined as follows:

$$R_{SRH} = \frac{np - n_i^2}{(n + n_i e^{E^*/k_BT})\tau_p + (p + n_i e^{-E^*/k_BT})\tau_n} \tag{6.2}$$

$E^* = E_{trap} - (E_c + E_v)/2$ is the trap level with respect to the midband energy. n_i is the intrinsic carrier density, τ_n and τ_p are the recombination times. The parameters are taken

Elemental quantities		
`EField`	Electric Field	Vcm^{-1}
`GradFermiE`	Gradient of the electron electro-chemical potential	Vcm^{-1}
`GradFermiH`	Gradient of the hole electro-chemical potential	Vcm^{-1}
`Current`	Total current density	Acm^{-2}
`eCurrent`	Electron current density	Acm^{-2}
`hCurrent`	Hole current density	Acm^{-2}
`Polarization`	Electric Polarization	Cm^{-2}
`GradPn`	Gradient of electron thermoelectric power	$\mathrm{VK}^{-1}\mathrm{cm}^{-1}$
`GradPp`	Gradient of hole thermoelectric power	$\mathrm{VK}^{-1}\mathrm{cm}^{-1}$

Table 6.2: Elemental quantities

Scalar quantities		
`ContactCurrents`	Contact currents	*[a]

[a] depends on dimension and symmetry

Table 6.3: Scalar quantities

from the material database. The recombination times are dependent on temperature and doping density, e.g.

$$\tau_n = \tau_n^0 \left(\frac{T}{T_0}\right)^{\alpha_n} \tag{6.3}$$

$$\tau_n^0 = \tau_{min,n} + \frac{\tau_{max,n} - \tau_{min,n}}{1 + (N/N_{ref})^{\gamma}} \tag{6.4}$$

where T_0 is the reference temperature (300 K). Table 7.2 shows the corresponding parameters for the material data files.

The recombination times and trap level can be overridden from the input file by using the keywords of table 6.5 in the appropriate `physical_model` section or in the `Region` section (the latter overrides the former).

Direct (radiative) recombination

The direct recombination model can be enabled in the input file by specifying

```
physical_model recombination
{
  model = srh
  ...
}
```

Listing 2: Declaration of SRH recombination model

parameter	*electrons*	*holes*
τ_{min}	taumin_e	taumin_h
τ_{max}	taumax_e	taumax_h
N_{ref}	Nref_e	Nref_h
γ	gamma_e	gamma_h
E^*	Etrap	
α	Talpha_e	Talpha_h

Table 6.4: SRH material data file parameters

```
physical_model recombination
{
  model = direct
  ...
}
```

Direct recombination is modeled as follows:

$$R_{direct} = C(np - n_i^2) \tag{6.5}$$

The material data file and the input file use the same keyword `C` for the parameter C. The database value can be overridden from the input file as described for SRH recombination.

tau_n	tau_n
tau_p	tau_p
E^*	E_t

Table 6.5: SRH input file parameters

6.3.2 Thermoelectric power models

The thermoelectric power models are the same for electrons and holes. The keywords is `thermoelectric_power`, i.e

```
physical_model thermoelectric_power
{
  model = ...
}
```

The model keyword can be `constant` (i.e. the thermoelectric powers are read from the database) or `diffusivity_model` where the thermoelectric powers are computed by

$$P_n = -\frac{k_b}{q}\left(\frac{5}{2} + \frac{e\phi_n + E_c - e\varphi}{k_b T}\right) \tag{6.6}$$

$$P_p = \frac{k_b}{q}\left(\frac{5}{2} - \frac{e\phi_p + E_v - e\varphi}{k_b T}\right) \tag{6.7}$$

The default is $P_n = P_p = 0$.

6.3.3 Mobility models

Mobility models have currently to be defined for electrons and holes independently. The corresponding keywords are `electron_mobility` and `hole_mobility`, i.e.

```
physical_model electron_mobility
{
  model = ...
  ...
}

physical_model hole_mobility
{
  model = ...
  ...
}
```

The default model is the constant mobility model.

Constant mobility model

The constant mobility model (identifier `constant`) assumes a mobility which depends only on temperature by means of the following formula:

$$\mu_{const} = \mu_0 (T/T_0)^{-\gamma} \tag{6.8}$$

In the material data file μ_0 and γ have to be specified with the keywords `mu_max_e`, `mu_max_h` and `exponent_e`, `exponent_h`, respectively. μ_0 can be ovverridden from the `physical_model` section using the keyword `mu` or from the `Region` sections using the keywords `mu_e` and `mu_h`.

Doping dependent mobility model

The doping dependent mobility model (identifier `doping_dependent`) implements two models for mobility depending on the total doping density and the temperature. The model that is used depends on the value of the `mobility_formula` parameter.

Model by Masetti et al. [4]
The model by Masetti et al. is identified by `mobility_formula = 1`. It uses the following formula:

$$\mu = \mu_{min,1} * \mathrm{e}^{-P_c/N} + \frac{\mu_{const} - \mu_{min,2}}{1 + (N/C_r)^{\alpha}} - \frac{\mu_1}{1 + (C_s/N)^{\beta}} \tag{6.9}$$

where N is the total doping density and μ_{const} the mobility obtained from the constant mobility model. The parameters are specified as given in table 6.6.

parameter	*electrons*	*holes*
$\mu_{min,1}$	`mumin1_e`	`mumin1_h`
$\mu_{min,2}$	`mumin2_e`	`mumin2_h`
μ_1	`mu1_e`	`mu1_h`
P_c	`Pc_e`	`Pc_h`
C_r	`Cr_e`	`Cr_h`
C_s	`Cs_e`	`Cs_h`
α	`alpha_e`	`alpha_h`
β	`beta_e`	`beta_h`

Table 6.6: Data file parameters for the mobility model by Masetti et al.

Model by Arora [5]

The model by Arora is identified by `mobility_formula = 2`. It reads:

$$\mu = \mu_{min} + \frac{\mu_d}{1 + (N/N_0)^{A^*}} \tag{6.10}$$

with

$$\mu_{min} = A_{min}(T/T_0)^{\alpha_m}, \quad \mu_d = A_d(T/T_0)^{\alpha_d}$$
$$N_0 = A_N(T/T_0)^{\alpha_N}, \quad A^* = A_a(T/T_0)^{\alpha_a}$$

The parameters are given in table 6.7.

parameter	*electrons*	*holes*
A_{min}	`mumin_e`	`mumin_h`
A_d	`mud_e`	`mud_h`
A_N	`N0_e`	`N0_h`
A_a	`a_e`	`a_h`
α_m	`am_e`	`am_h`
α_d	`ad_e`	`ad_h`
α_N	`an_e`	`an_h`
α_a	`aa_e`	`aa_h`

Table 6.7: Data file parameters for the mobility model by Arora.

Field dependent mobility model

Currently one mobility model depending on the modulus of the electric field is implemented (identifier `field_dependent`). It is based on the Caughey-Thomas model, refined by Canali [6]:

$$\mu = \frac{\mu_{lowfield}}{\left(1 + \left(\frac{\mu_{lowfield}|\mathbf{E}|}{v_{sat}}\right)^{\beta}\right)^{1/\beta}} \tag{6.11}$$

with

$$\beta = \beta_0(T/T_0)^b$$

$|\mathbf{E}|$ is the modulus of the electric field, $\mu_{lowfield}$ is the low-field mobility. For the latter one can specify the model to be used using the parameter `lowfield_model`. As default the doping dependent model is used.

There are two models for v_{sat}, identified with `Vsat_Formula = 1` and `2`. Formula 1 reads

$$v_{sat} = v_{sat,0}(T/T_0)^{-\gamma}$$

Formula 2 reads

$$v_{sat} = \max(A_{vsat} - B_{vsat}(T/T_0), v_{min})$$

The parameters for the field dependent mobility model are summarized in table 6.8.

parameter	*electrons*	*holes*
β_0	`beta0_e`	`beta0_h`
b	`betaexp_e`	`betaexp_h`
$v_{sat,0}$	`vsat0_e`	`vsat0_h`
γ	`vsatexp_e`	`vsatexp_h`
A_{vsat}	`A_vsat_e`	`A_vsat_h`
B_{vsat}	`B_vsat_e`	`B_vsat_h`
v_{min}	`vsat_min_e`	`vsat_min_h`

Table 6.8: Data file parameters for the mobility model by Arora.

6.3.4 Boundary conditions

Boundary conditions are implemented for ohmic contacts, Schottky contacts and free surfaces. Contacts are boundary models that allow a nonzero normal electrical current. For this type of boundaries one can define a contact resistance using the `contact_resistance` option. The contact resistance has units Ωcm^2. The applied voltage is specified with the option `voltage`. A variable can be assigned to this, using the `@`-syntax.

For a finer control of the behaviour at electrical contacts, the options `zero_field`, `zero_grad_fermi_e` and `zero_grad_fermi_h` can be used, which when set to `true` will impose zero normal electric field and zero normal gradient of the electron and hole electro-chemical potential, respectively.

The ohmic contact (identifier `ohmic`) has no further parameters.

A Schottky contact (identifier `schottky`) has the additional parameter `barrier`, which signifies the energy difference between the semiconductor band edge and the fermi energy in the metal. As default, the barrier is taken with respect to the conduction band. By specifying `band = v` the barrier can be imposed with respect to the valence band (p-type contact).

The type of boundary model is chosen by the parameter `type`, e.g. `type = schottky`.

The free surface or interface model (identifier `interface`) models surface charges. Two modes are possible:

constant charge a constant charge can be assigned by specifying only the sheet carrier density `Ns` in cm^{-2}. The sheet charge density will then equal `Ns` multiplied by the elementary charge e. A positive `Ns` produces a positive surface charge.

electronic surface states in this case the surface charge is produced by electrons occupying a surface state with a density of states in form of a delta function. The density of occupied states then reads

$$n_s = \frac{N_s}{1 + \frac{1}{g}\exp(\frac{E_c - \Delta E_s - e\varphi + e\phi_n}{k_B T})}$$

The density of states N_s is specified by `Ns`, the energy of the state with respect to the conduction band ΔE_s by `Es`. g denotes the multiplicity of the state and defaults to 2. It can be changed by assigning a value to `g`.

6.4 `Physics` section

Options for controlling the drift-diffusion semiconductor models can be specified in the `Physics` section. The corresponding paramaters are given in table 6.9. When `model` is

keyword	*possible values*	*description*
`model`	(see following subsections)	the model to use for the description of the conduction and valence band properties
`statistics`	`B` | `FD`	Boltzmann (default) or Fermi-Dirac statistics
`strain_simulation`	*name*	the strain simulation to be used
`thermal_simulation`	*name*	the thermal simulation to be used
`electron_quantum_density`	*name*	the quantum density simulation to be used for the electron density
`hole_quantum_density`	*name*	the quantum density simulation to be used for the hole density

Table 6.9: Common options for the drift-diffusion semiconductor models

not specified, the default semiconductor model based on bulk $\mathbf{k} \cdot \mathbf{p}$ theory is used.

The `electron_quantum_density` and `hole_quantum_density` will use the particle densities calculated from the corresponding `quantum_density` simulation. In regions where no quantum density is available, the classical density will be used. The `electron_quantum_density` and `hole_quantum_quantum_density` keywords can be used also in the `Region` sections to be able to use different quantum density simulations in different regions.

The `strain_simulation` option is used to specify the simulation that provides strain in the case of strained systems. If it is omitted, an unstrained system is assumed for the drift-diffusion calculation.

The `thermal_simulation` option is used to specify the simulation that provides the lattice temperature for non-isothermal simulations. If it is omitted, the simulation temperature as provided in the `Simulation` section of the input file (or, if not provided, the default value of 300 K) is used.

6.4.1 Simple semiconductor model

When specifying `model = simple` a very simple semiconductor model is used. For this model one has to provide conduction and valence band edges and the effective density of states masses in the `Region` sections. The corresponding keywords are given in table 6.10.

keyword	*description*
`Ec`	conduction band edge (eV)
`Ev`	valence band edge (eV)
`m_dos_e`	conduction band effective DOS mass (m_e)
`m_dos_h`	valence band effective DOS mass (m_e)

Table 6.10: Parameters for the simple semiconductor model

6.4.2 Default semiconductor model

The default semiconductor model uses a bulk $\mathbf{k}\cdot\mathbf{p}$ model to calculate the band parameters. It can be chosen explicitly by `model = default`. The model reads all needed parameters from the material data file.

The band parameters are calculated considering locally strain and lattice temperature as obtained from the corresponding simulations specified using the `strain_simulation` and `thermal_simulation` keywords.

6.5 `Solver` section

Many of parameters for the numerical solver depend on the type of solver being used and on the device to be simulated. Table 6.11 lists the options that are independent on the type of solver used.

The linear and nonlinear solvers to be used can be chosen using the keywords `linear_solver` and `nonlinear_solver`, respectively. For the nonlinear solver one can chose between

keyword	*description*[a]
`coupling`	defines which equations to couple together. `poisson`: solve only poisson eq., `electrons`: electrons and poisson, `holes`: holes and poisson, `current`: only electron and hole currents, `<full>`: the fully coupled system
`integration_order`	order of the numerical gauss integration. Default is `2`
`current_integration_method`	method for the calculation of the contact cutrrents. `surfint`: integrate the local current density over the contact surface, `<rstf>`: use the Ramo-Shockley test functions, gives better results
`local_scaling`	apply a local scaling scheme which leads to better scaled matrices. `<true>` or `false`
`exact_newton`	use exact or approximate (without some parts in the jacobian) Newton. `<true>` or `false`

[a]the default is given in brackets

Table 6.11: Parameters for the PETSc nonlinear solver

the PETSc implementation (`petsc`) and the TiberCAD implementation (`tiber`) of line search. When using the TiberCAD nonlinear solver, one can additionally chose between the PETSc (`petsc`) or PARDISO (`pardiso`) linear solvers. The possible combinations are:

```
nonlinear_solver = petsc
```

or

```
nonlinear_solver = tiber
linear_solver = petsc | pardiso
```

6.5.1 Parameters for PETSc solvers

Tables 6.12 and 6.13 list all solver parameters significant for the PETSc linear and nonlinear solvers. A more detailed description of the most important parameters follows.

The `ksp_type` specifies the type of Krylov subspace method to be used. The mostly used methods are

keyword	*description*	*default*
`nonlin_rel_tol`	relative tolerance for the residual l_2-norm (with respect to first nonlinear step)	`10e-9`
`nonlin_abs_tol`	absolute tolerance for the residual l_2-norm	`10e-15`
`nonlin_step_tol`	tolerance for the l_2-norm of the nonlinear step	`10e-3`
`ls_max_step`	the maximum l_2-norm for the line search step, in units of eV	`1`
`nonlin_max_it`	maximum number of nonlinear iterations	`20`

Table 6.12: Parameters for the PETSc nonlinear solver

keyword	*description*	*default*
`ksp_type`	the linear solver type	`bcgsl`
`pc_type`	the preconditioner type	`ilu`
`lin_rel_tol`	relative tolerance for the linear solver	`1e-6`[a]
`lin_abs_tol`	absolute tolerance for the linear solver	`10e-50`
`lin_max_it`	maximum number of linear iterations	`500`

[a]The linear tolerance gets automatically decreased after each nonlinear step.

Table 6.13: Parameters for the PETSc linear solver

`bcgs` A stabilized version of the biconjugate gradient method. This one works better in 1D than `bcgsl`.

`bcgsl` (default) A modified version of `bcgs`.

`gmres` Generalized minimal residual method.

The `pc_type` specifies the type of preconditioner to be used. The most useful ones are

`ilu` (default) Incomplete LU factorization. Does not work for materials with high band gap.

`jacobi` Jacobi preconditioning (diagonal scaling).

`composite` Combination of `ilu` and `jacobi`.

The `ls_max_step` parameter defines an upper bound of the l_2-norm of the nonlinear line search step. It should be not too big to prevent the algorithm from diverging, but

also not too small to minimize the number of iterations. Values between 1 and 10 should be a good choice.

The `nonlin_step_tol` defines at which line search step size (in l_2-norm) the algorithm stops, i.e. assumes to have reached convergence. `nonlin_step_tol` is measured in eV.

6.5.2 Parameters for the TiberCAD nonlinear solver

Table 6.14 summarizes the parameters used for the TiberCAD implementation of the line search algorithm.

keyword	*description*	*default*
`nonlin_rel_tol`	relative tolerance for the residual l_2-norm (with respect to first nonlinear step)	`10e-9`
`nonlin_abs_tol`	absolute tolerance for the residual l_2-norm	`10e-15`
`nonlin_step_tol`	tolerance for the maximum norm of the nonlinear step (eV)	`10e-3`
`nonlin_max_it`	maximum number of nonlinear iterations	`20`

Table 6.14: Parameters for the TiberCAD line search

The stopping criterion based on the line search step uses the maximum norm of the nonlinear step, i.e. convergence is controlled locally. In addition to the parameters in table 6.14 one has to provide also parameters for the linear solver.

6.5.3 Parameters for the PARDISO linear solver

NOTE: the PARDISO linear solver is currently not included in the distribution. Currently the PARDISO interface has no adjustable parameters.

Chapter 7

Heat Balance simulation

The theoretical model of the heat balance problem can be found in Ref.[7].

7.1 Heat equation

The steady state heat equation with the continuity equation reads as

$$\nabla \cdot (-\kappa \nabla T) = H_S \tag{7.1}$$

where T is the temperature, κ is the thermal conductivity tensor and H_S is the total heat source. The latter term is the sum of the heat sources specified by the submodels described below. The term between the brackets represents the thermal flux $\mathbf{J_q}$.

7.2 Physical model

By neglecting particle effects, the thermal conductivity is only due to the lattice contribution. The lattice thermal conductivity is read from the database.

The thermal model is tagged as *thermal*. In **options** subsection we indicate the simulation name (*simulation_name = whatever_you_want*) and the simulation domain (*physical_regions = wherever_you_want*)

```
model thermal
 {

  options
  {
    simulation_name = whatever_you_want
```

```
    physical_regions = wherever_you_want
  }

    ...
}
```

7.2.1 Electron and hole dissipations

Electron and hole dissipations give the following heat source

$$H_S = -\nabla \cdot [(P_n T + \phi_n)\mathbf{J_n} + (P_p T + \phi_p)\mathbf{J_p}] \tag{7.2}$$

where P_n and P_p are the thermoelectric power of electrons and holes, respectively. ϕ_n and ϕ_p are the electro-chemical potentials.

The equation 7.2 represents severals heat source contributions. Their estimates are reported in table 7.1.

Expression	*Heat source*
$\frac{\lvert\mathbf{J_n}\rvert^2}{\sigma_n}$	*Electron Joule effect*
$\frac{\lvert\mathbf{J_p}\rvert^2}{\sigma_p}$	*Hole Joule effect*
$qR_{SRH}\left(\phi_p - \phi_n + T\left(P_p - P_n\right)\right)$	*Recombination effect*
$-T\mathbf{J_n} \cdot \nabla P_n$	*Electron Peltier-Thomson effect*
$-T\mathbf{J_p} \cdot \nabla P_p$	*Hole Peltier-Thomson effect*

Table 7.1: Drift diffusion heat sources

The physical model **heat_source** includes a specific source identified by its **model** name. Concerning electron and hole dissipations the model is named *drift_diffusion_dissipation*, as reported below.

```
physical_model heat_source
{
  model = drift_diffusion_dissipation

  drift_diffusion_simulation = dd_simul_name
}
```

In order to include such a heat source we have to use a drift diffusion simulation. The syntax *drift_diffusion_simulation = dd_simul_name* allows this connection.

7.2.2 Boundary conditions

By default, thermally insulating surfaces are considered, i.e.

$$\mathbf{J_q} \cdot \mathbf{N} = 0 \tag{7.3}$$

On the opposite side it is possible to include an ideal thermally conducting interface by fixing the temperature to the external one, i.e. :

$$T = T_{ext} \tag{7.4}$$

This condition can be imposed with the following notation

```
BC_Regions
{
  BC_Region name_BC_region
  {
    type = heat_reservoir
    BC_reg_numb = 3
    temperature = 300
  }
}
```

Once a `BC_Region` is inserted in the `thermal` section, `heat_reservoir` is the default `type`. The default `temperature` is the one indicated in the solve section.

Between such extreme situations, it is possible to take into account a thermally resistive interface, i.e.

$$\mathbf{J_q} \cdot \mathbf{N} = G_s(T - T_{ext}) \tag{7.5}$$

where G_s is the thermal surface conductance and T_{ext} is the external temperature.

One can include this condition with the BC type **thermal_surface_conductance**:

```
BC_Regions
{
  BC_Region name_BC_region
  {
    type = thermal_surface_conductance
    BC_reg_numb = 3
    g_surf = 0.01
    temperature = 300
  }
}
```

where `g_surf` indicates G_s and `temperature` stands for T_{ext}.

Alternatively, it is possible to indicate the $R_s = 1/G\_s$ quantity i.e. the thermal surface resistance. The notation is

```
BC_Regions
{
  BC_Region name_BC_region
  {
    type = thermal_surface_resistance
    BC_reg_numb = 3
    r_surf = 100
    temperature = 300
  }
}
```

Furthermore, it is possibile to fix the normal thermal power density to a given value J_{ext}, i.e.

$$\mathbf{J_q} \cdot \mathbf{N} = J_{ext} \tag{7.6}$$

This condition is set with the BC type **thermal_flux**:

```
BC_Regions
{
  BC_Region name_BC_region
  {
    type = thermal_flux
    BC_reg_numb = 3
    power_density = 100
  }
}
```

7.3 Output data

The variable labels are listed in the tables 7.3-7.5.

It is also possible to identify all heat sources with the keyword `HeatSource` and all power fluxes with `PowerFlux`. Finally, with the keyword `thermal` all quantities concerning the thermal simulation will be stored.

description	*type*	*parameters*	*units*
Ideal insulating interface	(Default)	(No parameters)	
Ideal conducting interface	`heat_reservoir`	`temperature`	K
Resistive interface	`thermal_surface_resistance`	`temperature`	K
		`r_surf`	cm^2KW^{-1}
Resistive interface	`thermal_surface_conductance`	`temperature`	
		`g_surf`	$WK^{-1}cm^{-2}$
Power density condition	`thermal_flux`	`power_density`	Wcm^{-2}

Table 7.2: Thermal boundary conditions

Nodal scalar quantities

`LatticeTemp`	Temperature	K

Table 7.3: Nodal scalar quantities

Elemental scalar quantities

`eJoule`	Electron Joule effect	Wcm^{-3}
`hJoule`	Hole Joule effect	Wcm^{-3}
`RecHeat`	Recombination heat	Wcm^{-3}
`ePelTh`	Electron Peltier-Thomson effect	Wcm^{-3}
`hPelTh`	Hole Peltier-Thomson effect	Wcm^{-3}
`TotalHeat`	TotalHeat	Wcm^{-3}

Table 7.4: Elemental scalar quantities

Elemental vector quantities

`Wq`	Thermal flux	Wcm^{-2}
`Wn`	Electron power flux	Wcm^{-2}
`Wp`	Hole power flux	Wcm^{-2}
`W`	Total power flux	Wcm^{-2}

Table 7.5: Elemental vector quantities

Chapter 8

Envelope Function Approximation

The envelope function appriximation (EFA) simulation tool of TiberCAD is developed in order to solve a single-particle Schrödinger equation for electrons and holes in a semiconductor crystal. This problem is an eigenvalue problem that is treated as a generalized complex eigenvalue problem

$$H\psi = S\psi, \tag{8.1}$$

where H and S are the Hamiltonian and S-matrix, respectively.

8.1 Models section parameters

The **Models** section looks like follows:

```
model efaschroedinger
{
    options
    {
     simulation_name = quantum_well1
     physical_regions = (1,2)
    }

}
```

The default boundary conditions of the simulation domain are open (that is zero flux for single-band calculation). It is possible to specify Dirichlet boundary conditions:

```
BC_Region infinite_barrier1
{
     BC_reg_numb = 12
```

```
    type = Dirichlet
}
```

There is a way to impose automatically the Dirichlet boundary conditions over all the boundary of the simulation region. This is done by the parameter

Dirichlet_bc_everywhere = {true | false} in **Solver** section. The default value for EFA problem is true.

8.2 Solver parameters

There are two groups of parameters. The first group is related to the general eigensolver problem, the second one is related to the Schrödinger equation.

8.2.1 Eigenvalue problem parameters

These parameters are common for all eigenvalue problems. Their default values may be different for different eigenvalue problems, for example for the Schroedinger equation and for the electromagnetic eigenvalue problem.

The eigenvalue problem can be solved by the solvers that are implemented into the SLEPc library. The relative parameter is

solver = { arnoldi | lapack | krylovshur }. The default value is `krylovshur`.

In the case of the lapack solver all the eigenvalues are computed. In the case of arnoldi or krylovshur solver it is necessary to specify which and how many eigenvalues have to be computed. The idea is that the iterative solver calculates several eigenvalues that a close to a specific number, reffered to as the *spectral_shift*. The relative parameters are:

max_iteration_number	maximum number of iteration, used as a stop condition
eigen_solver_tolerance	numerical eigensolver tolerance used as a convergence criteria
spectral_shift	the closest eigenvalues to this value (eV) are found.
spectrum_inversion_tolerance	tolerance used for linear solver

Table 8.1: Iterative eigensolver parameters

If the spectral_shift is not defined then it will be calculated internally from the band edges.

For the iterative solvers the important parameters, that may significantly change the performance, are the *Krylov subspace method* type and the *preconditioner* type.

The Krylov method is defined as follows:
ksp_type = { bcgsl | gmres | bcgs | cg | richardson | preonly }

The **preconditioner** type is defined as follows:
pc_type = { cholesky | jacobi | ilu | composite }
Other options:

- *x-periodicity* = { true | **false**}
- *y-periodicity* = { true | **false**}
- *z-periodicity* = { true | **false**}
- *number_of_eigenstates* = number of eigenstates to be computed

8.2.2 Schrödinger equation parameters

- *particle* = { el | hl }; specifies a particle type, according to each the eigenvalues are sorted
- *strain_model_name* = name of the simulation that can provide elastic strain
- *poisson_model_name* = name of the simulation that can provide electric and electrochemical potential
- *heat_model* = name of the simulation that can provide
- *relative_density_tolerance* = relative tolerance for charge density calculation
- *initial_eigenstates_number* = initial eigenstates number for charge density calculation
- *convergent_density* = { true | **false** } if true than number of eigenstates will be increased in oder to reach convergent density.
- *eigen_number_increase_factor* = factor to increase eigenvalues number for the next charge density calculation

8.3 Physical Models parameters

- *particle* = {el | hl }
- *model* = { conduction_band | kp } single conduction band (Γ point) or $\mathbf{k} \cdot \mathbf{p}$.
- *kp_model* = { 6×6 | 8×8 }

Here, the *particle* name is the name of a particle type (*electron* or *hole*).
model = **kp** | **conduction_band** : $\mathbf{k} \cdot \mathbf{p}$ or single conduction band model.
If $\mathbf{k} \cdot \mathbf{p}$ model is applied, specify:
kp_model = **6x6** | **8x8**.

8.4 Output

- **EigenEnergy** Eigen energy in eV
- **EigenFunctions** $|\psi(\mathbf{r})|^2$ function of the eigenstate
- **Occupation** probability to find the state occupied. It is calculated assuming Fermi distribution and mean electrochemical potential and temperature:

$$\bar{\mu} = \langle \psi | \mu(\mathbf{r}) | \psi \rangle \tag{8.2}$$
$$\bar{T} = \langle \psi | T(\mathbf{r}) | \psi \rangle \tag{8.3}$$

- **EnergyLevels** graphical output used for showing the energy level over the band diagram

Chapter 9

Simulation opticskp

By defining the **opticskp** model, calculation of optical properties is enabled; in particular, the optical kp matrix elements are calculated from the quantum models specified in **Solver** section:

```
opticskp
{
    initial_state_model = QW1_electrons # quantum_el
    final_state_model =   QW1_holes # quantum_hl
    initial_eigenstates = (0, 19)
    final_eigenstates   = (0, 19)
}
```

Here, *initial_state_model* and *final_state_model* are, respectively, the quantum models (**efaschroedinger** model) associated respectively to the initial state of optical transition (e.g. electron), and to the final state of optical transition (e.g. hole). *initial_eigenstates* and *final_eigenstates* refer to the range of eigenstates to be taken in account for optical calculations. By specifying, in **Solver** section, a range of energy values in this way:

```
Emin = 3.0
Emax  = 5.0
dE = 0.001
```

the emission optical spectrum for $\mathbf{k}$=0 is calculated. The spectrum is calculated in the following way:

$$P(\hbar\omega) = \sum_{i,j} \frac{1}{2\pi^2} \frac{\omega_{ij}^2 e^2}{m^2 c^3} |\mathbf{M_{i,j}e}|^2 f_i(E_i)(1 - f_j(E_j)) \frac{\Gamma/2}{(\hbar\omega_{ij} - \hbar\omega)^2 + (\Gamma/2)^2} d\Omega, \qquad (9.1)$$

where f_i and f_j are the Fermi distributions.

9.1 Output

The output variables for optics calculations are:

- **optical_spectrum_k_0** : optical emission spectrum for**k**=0, calculated through **opticskp** model

Chapter 10

Simulation opticalspectrum

By defining the model **opticalspectrum**, optical matrix elements are used to calculate the associated (emission) spectrum with a k-space integration. In **Solver** section:

```
opticalspectrum
{
    k_space_dimension = 2
    k-space_basis = true
    k1 = (0, 0, 0.1)
    k2 = (0, 0.1, 0)

    refine_fraction =  0.30
    relative_accuracy =  0.01
    refine_k_space = true

    number_of_nodes = (2, 2)
    wedge = quarter

    optical_matr_elem_model = opticskp

    polarization =  (0, 0, 1)

    Emin = 3.0
    Emax  = 5.0
    dE = 0.001
}
```

The parameters:

k_space_dimension = **1** for 2D simulations, **2** for 1D simulations. k-*space_basis* is **true** if the k-space is defined by means of k-vectors; if **false**, vectors are expressed in real space

If *refine_k_space* = **true**, that is adaptive k-mesh refinement is enabled, all the elements whose error is greater than the value (1-*refine_fraction*)* (maximum error) are going to be refined. In this case, 'Error' is just the integrated quantity. The refinement will end when the *relative_accuracy* is obtained.

number_of_nodes = numb. of elememts in k mesh, along each direction
wedge = half | quarter, to reduce calculation time, by exploiting symmetry.
optical_matr_elem_model = name of the *opticskp* model associated
polarization = light polarization (vector)
Emin, *Emax*, *dE* : energy range and step of spectrum calculation.

10.1 Output

The output variables for optics calculations are:

- **optical_spectrum**: k-space integrated optical emission spectrum, calculated by **opticalspectrum** model

Chapter 11

Quantum dispersion

There is a possibility to calculate the dependence of quantum eigenstates on **k**-vector. Such dependence is called *dispersion*. The simulation name is **quantumdispersion**. Example:

```
model quantumdispersion
 {
   options
   {
     simulation_name = dispersion1D_el
     physical_regions = all
   }

 }
```

11.1 Solver options

The dispersion of quantum states is calculate at k-points that are nodes of the mesh in k-space.

- **quantum_simulation** name of the Schrödinger equation simulation
- **min_eigenvalue_number**, **max_eigenvalue_number**: the dispersion is calculated for the states number i , where

  max_eigenvalue_number $\geq i \geq$ min_eigenvalue_number

The rest of the parameters (wedge, k_space_dimension, etc...) define the k-space

```
dispersion1D_el
 {
   quantum_simulation = quantum_el
   min_eigenvalue_number = 0
   max_eigenvalue_number = 5

   wedge = half
   k_space_dimension = 1
   k1 = (0, 0.1, 0)
   number_of_nodes = (10)

 }
```

11.2 Output

The output variable name is **k-space_dispersion**.

Chapter 12

Quantum Density

```
dens_el
{
    k_space_dimension = 2
    k-space_basis = true
    k1 = (0, 0, 0.1)
    k2 = (0, 0.1, 0)
    number_of_nodes = (4,4)
    wedge = quarter
    refine_fraction = 0.20
    relative_accuracy = 0.01
    refine_k_space = true
    uniform_refinement = false
    mesh_order = FIRST

    quantum_simulation = quantum_el
    degeneracy = 2
    initial_eigenstates_number = 10
    analitic = false
}
```

- **quantum_simulation** name of the Schrödinger simulation
- **degeneracy** degeneracy of the quantum state
- **initial_eigenstates_number** initial number of eigenstates for the Schrödinger equation
- **analytic** = { true | false } If true then the density is calculated analytically or numerically

Analitcal calculation of density is done in the following way. For each eigenstate we calculate the effective mass assuming quadratic dispersion. Then the charge density is calculate as follows:

$$\rho_{1D}(\mathbf{r}) = g\frac{mkT}{2\pi\hbar^2}|\psi(\mathbf{r})|^2 \ln\left(1+\exp\left(\pm\frac{\mu-E}{kT}\right)\right) \tag{12.1}$$

$$\rho_{2D}(\mathbf{r}) = g|\psi(\mathbf{r})|^2\frac{1}{2}\sqrt{\left(\frac{mkT}{2\pi\hbar^2}\right)}F_{-1/2}\left(\pm\frac{\mu-E}{kT}\right), \tag{12.2}$$

where ρ_{1D} and ρ_{2D} are the 1D and 2D charge densities; m is the averaged mass (the mass is different for each quantized state and is position independent); g is the degeneracy of the states. The + sign is for electrons, the − sign is for holes.

Numerical calculation is done by the following formula:

$$\rho(\mathbf{r}) = \sum_n \frac{1}{(2\pi)^d}\int_{BZ}|\psi(\mathbf{r})|^2\frac{1}{1+\exp\left(\pm\frac{E-\mu}{kT}\right)}d\mathbf{k}_{\|} \tag{12.3}$$

The integration is performed on a mesh in the k-space.

12.1 Output

The output parameter is **quantum_density**.

Bibliography

[1] Michael Povolotskyi and Aldo Di Carlo, "Elasticity theory of pseudomorphic heterostructures grown on substrates of arbitrary thickness," *Journal of Applied Physics*, vol. 100, pp. 063514, 2006.

[2] Matthias Auf der Maur, Michael Povolotskyi, Fabio Sacconi, and Aldo Di Carlo, "Simulation of piezoresistivity effect in FETs," *J. Comp. Electronics*, vol. 5, pp. 323, 2006.

[3] Siegfried Selberherr, *Analysis and Simulation of Semiconductor Devices*, Springer-Verlag Wien New York, 1st edition, 1984.

[4] G. Masetti, M. Severi, and S. Solmi, "Modeling of carrier mobility against carrier concentration in Arsenic-,Phosphorus- and Boron-doped Silicon," *IEEE Trans. on Electron Devices*, vol. 30, pp. 764–769, 1983.

[5] N. D. Arora, J. R. Hauser, and D. J. Roulston, "Electron and Hole Mobilities in Silicon as a Function of Concentration and Temperature," *IEEE Trans. on Electron Devices*, vol. 29, pp. 292–295, 1982.

[6] C. Canali, G. Majni, R. Minder, , and G. Ottaviani, "Electron and hole drift velocity measurements in Silicon and their empirical relation to electric field and temperature," *IEEE Trans. on Electron Devices*, vol. 22, pp. 1045–1047, 1975.

[7] Gerhard K. Wachutka, "Rigorous thermodynamic treatment of heat generation and conduction in semiconductor device modeling," *IEEE Transaction on Computer-aided Design.*, vol. 9, pp. 11, 1990.